

2-Mbit (256K × 8) Serial (SPI) F-RAM

serial (SPI), 256K × 8, 40 MHz, industrial

Features

- 2-Mbit ferroelectric random access memory (F-RAM) logically organized as 256K × 8
 - High-endurance 100 trillion (10^{14}) read/writes
 - 151-year data retention (See **“Data retention and endurance”** on page 20)
 - NoDelay™ writes
 - Advanced high-reliability ferroelectric process
- Very fast SPI
 - Up to 40-MHz frequency
 - Direct hardware replacement for serial flash and EEPROM
 - Supports SPI mode 0 (0, 0) and mode 3 (1, 1)
- Sophisticated write protection scheme
 - Hardware protection using the Write Protect (\overline{WP}) pin
 - Software protection using Write Disable instruction
 - Software block protection for 1/4, 1/2, or entire array
- Device ID
 - Manufacturer ID and Product ID
- Low power consumption
 - 800 μ A active current at 1 MHz
 - 100 μ A (typ) standby current
 - 3 μ A sleep mode current
- Low-voltage operation: $V_{DD} = 2.0$ V to 3.6 V
- Industrial temperature: -40°C to $+85^{\circ}\text{C}$
- Packages
 - 8-pin small outline integrated circuit (SOIC) package
 - 8-pin dual flat no leads (DFN) package
- Restriction of hazardous substances (RoHS) compliant

Functional description

The FM25V20A is a 2-Mbit nonvolatile memory employing an advanced ferroelectric process. A ferroelectric random access memory or F-RAM is nonvolatile and performs reads and writes similar to a RAM. It provides reliable data retention for 151 years while eliminating the complexities, overhead, and system-level reliability problems caused by serial flash, EEPROM, and other nonvolatile memories.

Unlike serial flash and EEPROM, the FM25V20A performs write operations at bus speed. No write delays are incurred. Data is written to the memory array immediately after each byte is successfully transferred to the device. The next bus cycle can commence without the need for data polling. In addition, the product offers substantial write endurance compared with other nonvolatile memories. The FM25V20A is capable of supporting 10^{14} read/write cycles, or 100 million times more write cycles than EEPROM.

These capabilities make the FM25V20A ideal for nonvolatile memory applications, requiring frequent or rapid writes. Examples range from data collection, where the number of write cycles may be critical, to demanding industrial controls where the long write time of serial flash or EEPROM can cause data loss.

The FM25V20A provides substantial benefits to users of serial EEPROM or flash as a hardware drop-in replacement. The FM25V20A uses the high-speed SPI bus, which enhances the high-speed write capability of F-RAM technology. The device incorporates a read-only Device ID that allows the host to determine the manufacturer, product density, and product revision. The device specifications are guaranteed over an industrial temperature range of -40°C to $+85^{\circ}\text{C}$.

Logic block diagram

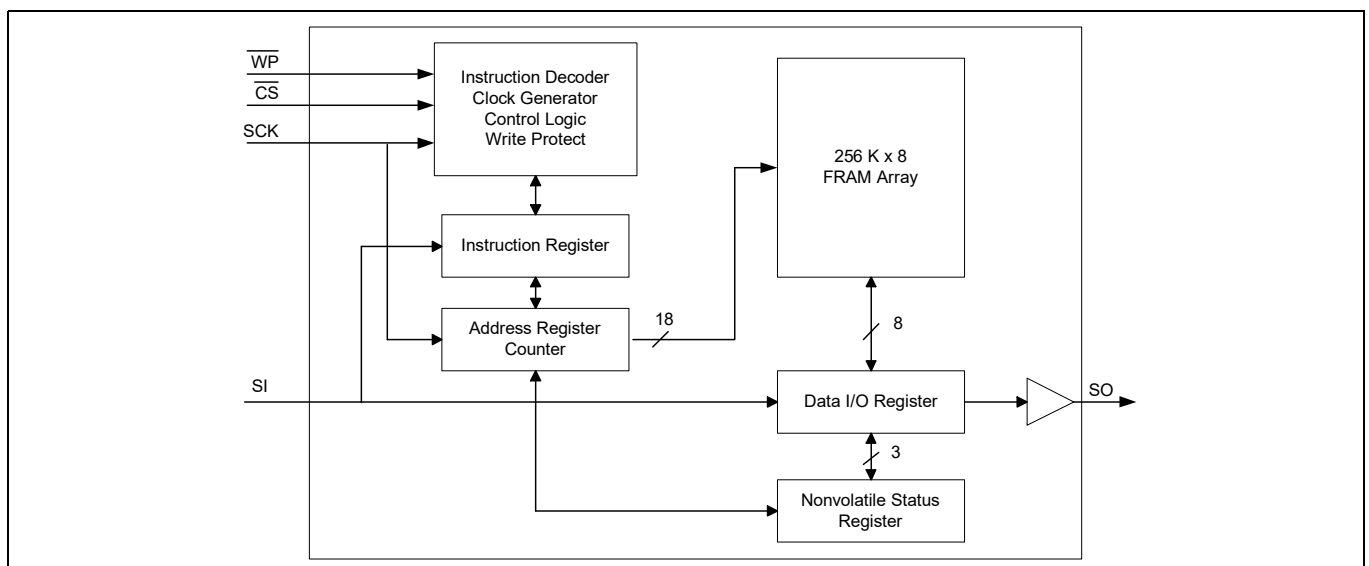


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Pinouts

1 Pinouts

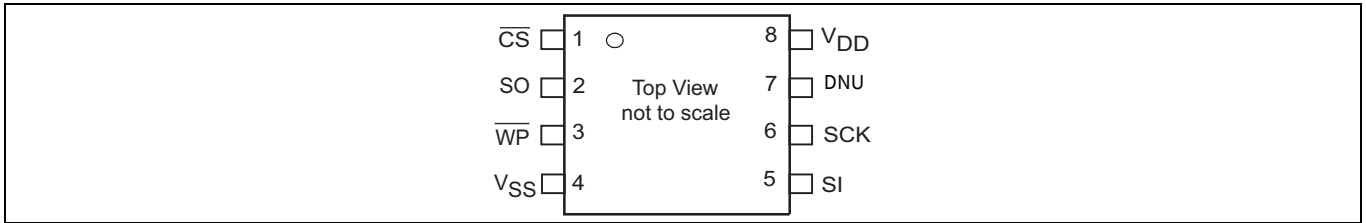


Figure 1 8-pin SOIC pinout

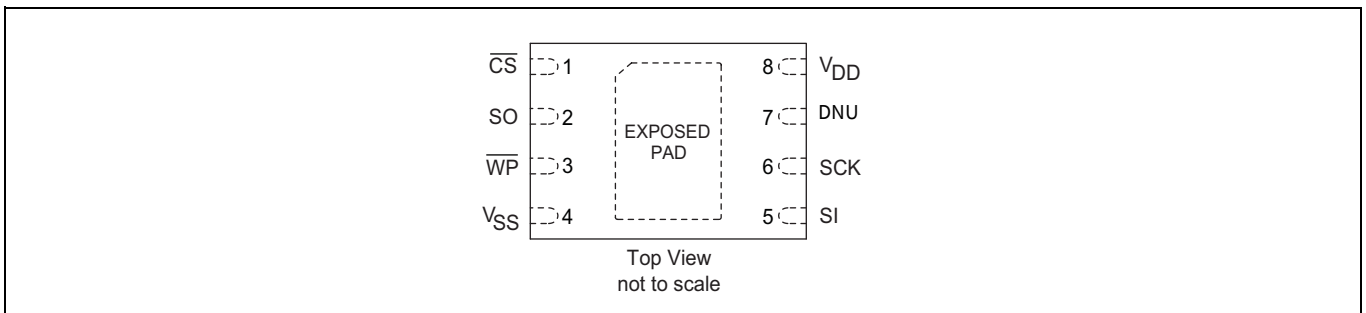


Figure 2 8-pin DFN pinout

2 Pin definitions

Table 1 Pin definitions

| Pin name | I/O type | Description |
|------------------------|--------------|---|
| $\overline{\text{CS}}$ | Input | Chip Select. This active LOW input activates the device. When HIGH, the device enters low-power standby mode, ignores other inputs, and the output is tristated. When LOW, the device internally activates the SCK signal. A falling edge on $\overline{\text{CS}}$ must occur before every opcode. |
| SCK | Input | Serial Clock. All I/O activity is synchronized to the serial clock. Inputs are latched on the rising edge and outputs occur on the falling edge. Because the device is synchronous, the clock frequency may be any value between 0 MHz and 40 MHz and may be interrupted at any time. |
| SI ^[1] | Input | Serial Input. All data is input to the device on this pin. The pin is sampled on the rising edge of SCK and is ignored at other times. It should always be driven to a valid logic level to meet IDD specifications. |
| SO ^[1] | Output | Serial Output. This is the data output pin. It is driven during a read and remains tristated at all other times. Data transitions are driven on the falling edge of the serial clock. |
| $\overline{\text{WP}}$ | Input | Write Protect. This Active LOW pin prevents write operation to the Status Register when WPEN is set to '1'. This is critical because other write protection features are controlled through the Status Register. A complete explanation of write protection is provided in " Status Register and Write Protection " on page 12. This pin must be tied to V_{DD} if not used. |
| DNU | Do Not Use | Do Not Use. This pin must be tied to V_{DD} . |
| V_{SS} | Power Supply | Ground for the device. Must be connected to the ground of the system. |
| V_{DD} | Power Supply | Power supply input to the device. |
| EXPOSED PAD | No Connect | The EXPOSED PAD on the bottom of 8-pin DFN package is not connected to the die. The EXPOSED PAD should not be soldered on the PCB. |

Note

1. SI may be connected to SO for a single pin data interface.

3 Functional overview

The FM25V20A is a serial F-RAM memory. The memory array is logically organized as 262,144 × 8 bits and is accessed using an industry-standard SPI bus. The functional operation of the F-RAM is similar to serial flash and serial EEPROMs. The major difference between the FM25V20A and a serial flash or EEPROM with the same pinout is the F-RAM's superior write performance, high endurance, and low power consumption.

3.1 Memory Architecture

When accessing the FM25V20A, the user addresses 256K locations of eight data bits each. These eight data bits are shifted in or out serially. The addresses are accessed using the SPI protocol, which includes a chip select (to permit multiple devices on the bus), an opcode, and a three-byte address. The upper 6 bits of the address range are 'don't care' values. The complete address of 18 bits specifies each byte address uniquely.

Most functions of the FM25V20A are either controlled by the SPI interface or handled by on-board circuitry. The access time for the memory operation is essentially zero, beyond the time needed for the serial protocol. That is, the memory is read or written at the speed of the SPI bus. Unlike a serial flash or EEPROM, it is not necessary to poll the device for a ready condition because writes occur at bus speed. By the time a new bus transaction can be shifted into the device, a write operation is complete. This is explained in more detail in the interface section.

3.2 Serial Peripheral Interface – SPI Bus

The FM25V20A is a SPI slave device and operates at speeds up to 40 MHz. This high-speed serial bus provides high-performance serial communication to a SPI master. Many common microcontrollers have hardware SPI ports allowing a direct interface. It is quite simple to emulate the port using ordinary port pins for microcontrollers that do not. The FM25V20A operates in SPI Mode 0 and 3.

3.3 SPI overview

The SPI is a four-pin interface with Chip Select (\overline{CS}), Serial Input (SI), Serial Output (SO), and Serial Clock (SCK) pins.

The SPI is a synchronous serial interface, which uses clock and data pins for memory access and supports multiple devices on the data bus. A device on the SPI bus is activated using the \overline{CS} pin.

The relationship between chip select, clock, and data is dictated by the SPI mode. This device supports SPI modes 0 and 3. In both of these modes, data is clocked into the F-RAM on the rising edge of SCK starting from the first rising edge after \overline{CS} goes active.

The SPI protocol is controlled by opcodes. These opcodes specify the commands from the bus master to the slave device. After \overline{CS} is activated, the first byte transferred from the bus master is the opcode. Following the opcode, any addresses and data are then transferred. The \overline{CS} must go inactive after an operation is complete and before a new opcode can be issued. The commonly used terms in the SPI protocol are as follows:

3.3.1 SPI Master

The SPI master device controls the operations on a SPI bus. An SPI bus may have only one master with one or more slave devices. All the slaves share the same SPI bus lines and the master may select any of the slave devices using the \overline{CS} pin. All of the operations must be initiated by the master activating a slave device by pulling the \overline{CS} pin of the slave LOW. The master also generates the SCK and all the data transmission on SI and SO lines are synchronized with this clock.

3.3.2 SPI Slave

The SPI slave device is activated by the master through the Chip Select line. A slave device gets the SCK as an input from the SPI master and all the communication is synchronized with this clock. An SPI slave never initiates a communication on the SPI bus and acts only on the instruction from the master.

The FM25V20A operates as an SPI slave and may share the SPI bus with other SPI slave devices.

3.3.3 Chip Select ($\overline{\text{CS}}$)

To select any slave device, the master needs to pull down the corresponding $\overline{\text{CS}}$ pin. Any instruction can be issued to a slave device only while the $\overline{\text{CS}}$ pin is LOW. When the device is not selected, data through the SI pin is ignored and the serial output pin (SO) remains in a high-impedance state.

Note: A new instruction must begin with the falling edge of $\overline{\text{CS}}$. Therefore, only one opcode can be issued for each active Chip Select cycle.

3.3.4 Serial Clock (SCK)

The Serial Clock is generated by the SPI master and the communication is synchronized with this clock after $\overline{\text{CS}}$ goes LOW.

The FM25V20A enables SPI modes 0 and 3 for data communication. In both of these modes, the inputs are latched by the slave device on the rising edge of SCK and outputs are issued on the falling edge. Therefore, the first rising edge of SCK signifies the arrival of the first bit (MSB) of a SPI instruction on the SI pin. Further, all data inputs and outputs are synchronized with SCK.

3.3.5 Data Transmission (SI/SO)

The SPI data bus consists of two lines, SI and SO, for serial data communication. SI is also referred to as Master Out Slave In (MOSI) and SO is referred to as Master In Slave Out (MISO). The master issues instructions to the slave through the SI pin, while the slave responds through the SO pin. Multiple slave devices may share the SI and SO lines as described earlier.

The FM25V20A has two separate pins for SI and SO, which can be connected with the master as shown in **Figure 3**.

For a microcontroller that has no dedicated SPI bus, a general-purpose port may be used. To reduce hardware resources on the controller, it is possible to connect the two data pins (SI, SO) together and tie off (HIGH) the $\overline{\text{WP}}$ pin. **Figure 4** shows such a configuration, which uses only three pins.

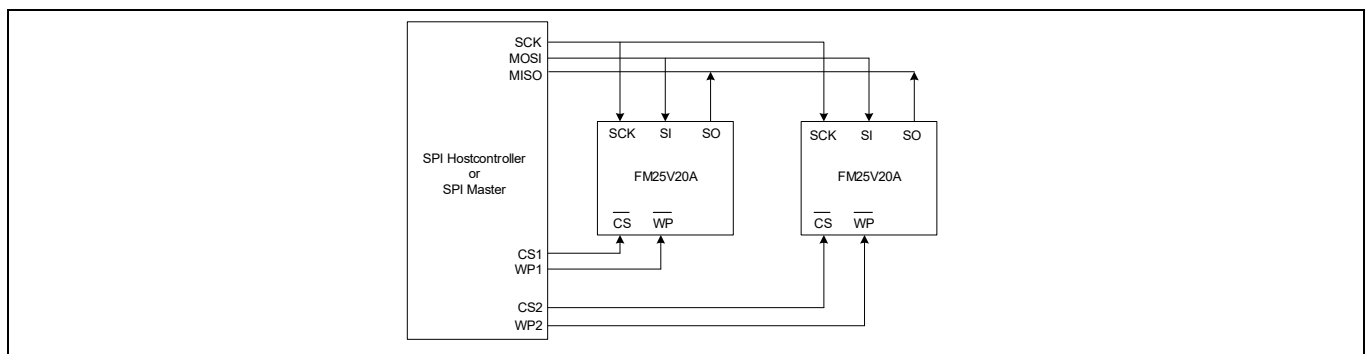


Figure 3 System Configuration with SPI Port

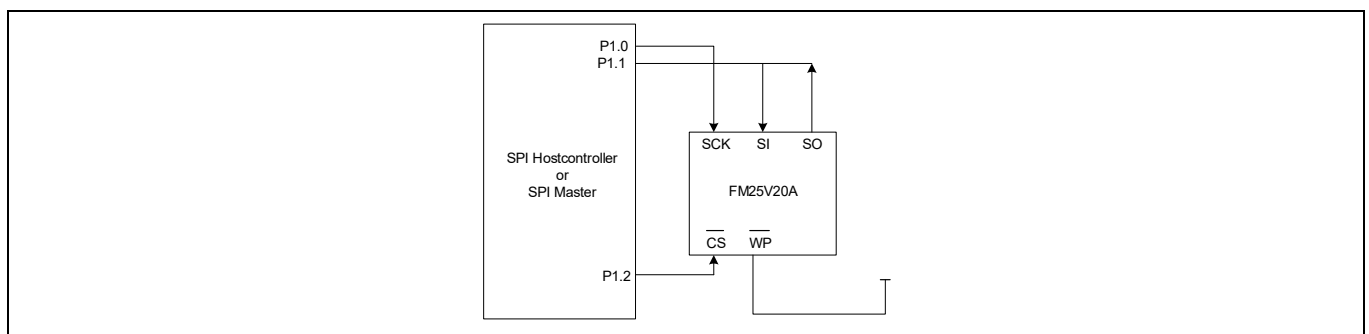


Figure 4 System Configuration without SPI Port

3.3.6 Most Significant Bit (MSB)

The SPI protocol requires that the first bit to be transmitted is the Most Significant bit (MSB). This is valid for both address and data transmission.

The 2-Mbit serial F-RAM requires a 3-byte address for any read or write operation. Because the address is only 18 bits, the first six bits, which are fed in are ignored by the device. Although these six bits are 'don't care', Infineon recommends that these bits be set to 0s to enable seamless transition to higher memory densities.

3.3.7 Serial Opcode

After the slave device is selected with \overline{CS} going LOW, the first byte received is treated as the opcode for the intended operation. FM25V20A uses the standard opcodes for memory accesses.

3.3.8 Invalid Opcode

If an invalid opcode is received, the opcode is ignored and the device ignores any additional serial data on the SI pin until the next falling edge of \overline{CS} , and the SO pin remains tristated.

3.3.9 Status Register

FM25V20A has an 8-bit Status Register. The bits in the Status Register are used to configure the device. These bits are described in [Table 4](#).

3.4 SPI Modes

FM25V20A may be driven by a microcontroller with its SPI peripheral running in either of the following two modes:

- SPI Mode 0 (CPOL = 0, CPHA = 0)
- SPI Mode 3 (CPOL = 1, CPHA = 1)

For both these modes, the input data is latched in on the rising edge of SCK starting from the first rising edge after \overline{CS} goes active. If the clock starts from a HIGH state (in mode 3), the first rising edge after the clock toggles is considered. The output data is available on the falling edge of SCK.

The two SPI modes are shown in **Figure 5** and **Figure 6**. The status of the clock when the bus master is not transferring data is:

- SCK remains at 0 for Mode 0
- SCK remains at 1 for Mode 3

The device detects the SPI mode from the status of the SCK pin when the device is selected by bringing the \overline{CS} pin LOW. If the SCK pin is LOW when the device is selected, SPI Mode 0 is assumed and if the SCK pin is HIGH, it works in SPI Mode 3.

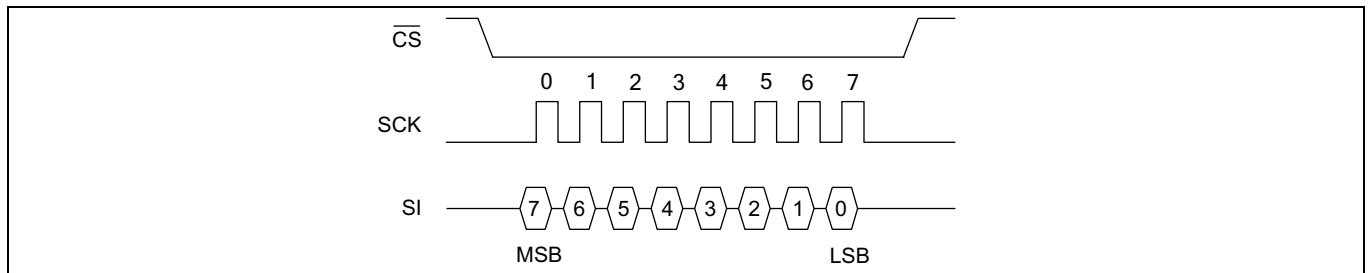


Figure 5 SPI Mode 0

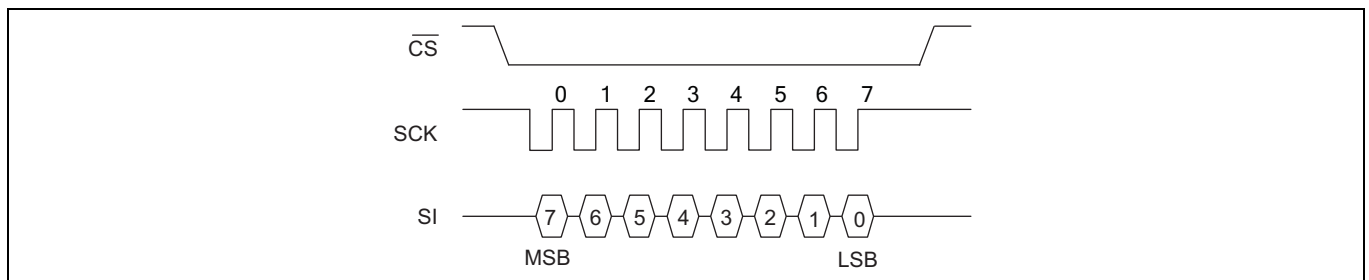


Figure 6 SPI Mode 3

3.5 Power Up to First Access

The FM25V20A is not accessible for a t_{PU} time after power-up. Users must comply with the timing parameter, t_{PU} , which is the minimum time from V_{DD} (min) to the first \overline{CS} LOW.

3.6 Command Structure

There are nine commands, called opcodes, that can be issued by the bus master to the FM25V20A. They are listed in [Table 1](#). These opcodes control the functions performed by the memory.

Table 2 Opcode Commands

| Name | Description | Opcode |
|-------|--------------------------|------------|
| WREN | Set write enable latch | 0000 0110b |
| WRDI | Reset write enable latch | 0000 0100b |
| RDSR | Read Status Register | 0000 0101b |
| WRSR | Write Status Register | 0000 0001b |
| READ | Read memory data | 0000 0011b |
| FSTRD | Fast read memory data | 0000 1011b |
| WRITE | Write memory data | 0000 0010b |
| SLEEP | Enter sleep mode | 1011 1001b |
| RDID | Read device ID | 1001 1111b |

3.7 WREN - Set Write Enable Latch

The FM25V20A will power up with writes disabled. The WREN command must be issued before any write operation. Sending the WREN opcode allows the user to issue subsequent opcodes for write operations. These include writing the Status Register (WRSR) and writing the memory (WRITE).

Sending the WREN opcode causes the internal Write Enable Latch to be set. A flag bit in the Status Register, called WEL, indicates the state of the latch. WEL = 1 indicates that writes are permitted. Attempting to write the WEL bit in the Status Register has no effect on the state of this bit – only the WREN opcode can set this bit. The WEL bit will be automatically cleared on the rising edge of \overline{CS} following a WRDI, a WRSR, or a WRITE operation. This prevents further writes to the Status Register or the F-RAM array without another WREN command. [Figure 7](#) illustrates the WREN command bus configuration.

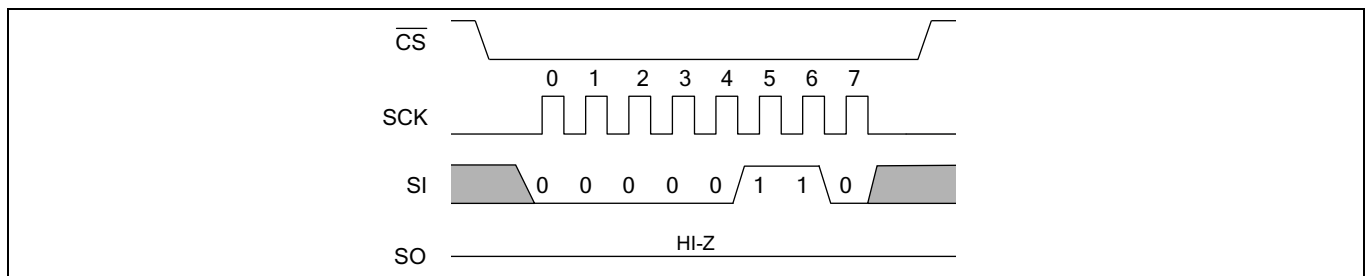


Figure 7 WREN Bus Configuration

3.8 WRDI - Reset Write Enable Latch

The WRDI command disables all write activity by clearing the Write Enable Latch. The user can verify that writes are disabled by reading the WEL bit in the Status Register and verifying that WEL is equal to '0'. [Figure 8](#) illustrates the WRDI command bus configuration.

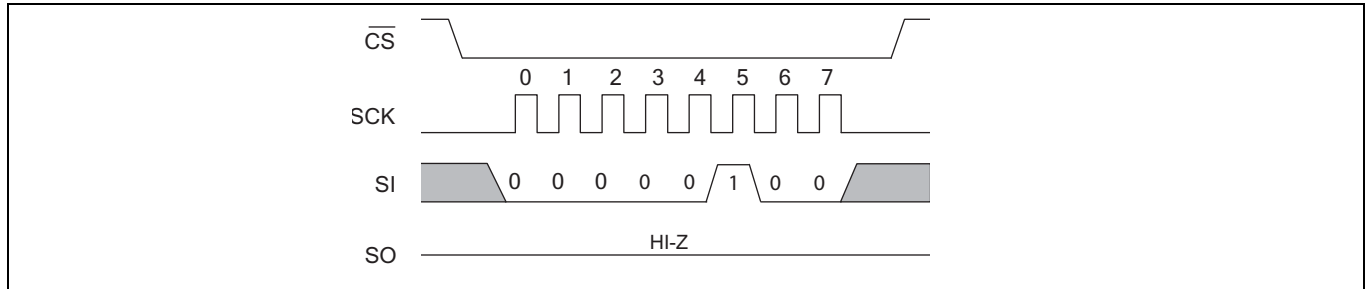


Figure 8 WRDI Bus Configuration

4 Status Register and Write Protection

The write protection features of the FM25V20A are multi-tiered and are enabled through the status register. The Status Register is organized as follows. (The default value shipped from the factory for WEL, BP0, BP1, bits 4–5, WPEN is ‘0’, and for bit 6 is ‘1’).

Table 3 Status Register

| Bit 7 | Bit 6 | Bit 5 | Bit 4 | Bit 3 | Bit 2 | Bit 1 | Bit 0 |
|----------|-------|-------|-------|---------|---------|---------|-------|
| WPEN (0) | X (1) | X (0) | X (0) | BP1 (0) | BP0 (0) | WEL (0) | X (0) |

Table 4 Status Register Bit definition

| Bit | Definition | Description |
|--------------|--------------------------|---|
| Bit 0 | Don't care | This bit is non-writable and always returns ‘0’ upon read. |
| Bit 1 (WEL) | Write Enable | WEL indicates if the device is write enabled. This bit defaults to ‘0’ (disabled) on power-up. WEL = 1 --> Write enabled WEL = 0 --> Write disabled |
| Bit 2 (BP0) | Block Protect bit ‘0’ | Used for block protection. For details, see Table 5 . |
| Bit 3 (BP1) | Block Protect bit ‘1’ | Used for block protection. For details, see Table 5 . |
| Bit 4–5 | Don't care | These bits are non-writable and always return ‘0’ upon read. |
| Bit 6 | Don't care | This bit is non-writable and always returns ‘1’ upon read. |
| Bit 7 (WPEN) | Write Protect Enable bit | Used to enable the function of Write Protect Pin (\overline{WP}). For details, see Table 6 . |

Bits 0 and 4–5 are fixed at ‘0’ and bit 6 is fixed at ‘1’; none of these bits can be modified. Note that bit 0 (“Ready or Write in progress” bit in serial flash and EEPROM) is unnecessary, as the F-RAM writes in real-time and is never busy, so it reads out as a ‘0’. An exception to this is when the device is waking up from sleep mode, which is described in “[Sleep Mode](#)” on page 15. The BP1 and BP0 control the software write-protection features and are nonvolatile bits. The WEL flag indicates the state of the Write Enable Latch. Attempting to directly write the WEL bit in the Status Register has no effect on its state. This bit is internally set and cleared via the WREN and WRDI commands, respectively.

BP1 and BP0 are memory block write protection bits. They specify portions of memory that are write-protected as shown in [Table 5](#).

Table 5 Block Memory Write Protection

| BP1 | BP0 | Protected Address Range |
|-----|-----|------------------------------|
| 0 | 0 | None |
| 0 | 1 | 30000h to 3FFFFh (upper 1/4) |
| 1 | 0 | 20000h to 3FFFFh (upper 1/2) |
| 1 | 1 | 00000h to 3FFFFh (all) |

The BP1 and BP0 bits and the Write Enable Latch are the only mechanisms that protect the memory from writes. The remaining write protection features protect inadvertent changes to the block protect bits.

The write protect enable bit (WPEN) in the Status Register controls the effect of the hardware write protect (\overline{WP}) pin. When the WPEN bit is set to ‘0’, the status of the \overline{WP} pin is ignored. When the WPEN bit is set to ‘1’, a LOW on the \overline{WP} pin inhibits a write to the Status Register. Thus the Status Register is write-protected only when WPEN = 1 and \overline{WP} = 0.

Table 6 summarizes the write protection conditions.

Table 6 Write Protection

| WEL | WPEN | WP | Protected Blocks | Unprotected Blocks | Status Register |
|-----|------|----|------------------|--------------------|-----------------|
| 0 | X | X | Protected | Protected | Protected |
| 1 | 0 | X | Protected | Unprotected | Unprotected |
| 1 | 1 | 0 | Protected | Unprotected | Protected |
| 1 | 1 | 1 | Protected | Unprotected | Unprotected |

4.1 RDSR - Read Status Register

The RDSR command allows the bus master to verify the contents of the Status Register. Reading the status register provides information about the current state of the write-protection features. Following the RDSR opcode, the FM25V20A will return one byte with the contents of the Status Register.

4.2 WRSR - Write Status Register

The WRSR command allows the SPI bus master to write into the Status Register and change the write protect configuration by setting the WPEN, BP0 and BP1 bits as required. Before issuing a WRSR command, the WP pin must be HIGH or inactive. Note that on the FM25V20A, WP only prevents writing to the Status Register, not the memory array. Before sending the WRSR command, the user must send a WREN command to enable writes. Executing a WRSR command is a write operation and therefore, clears the Write Enable Latch.

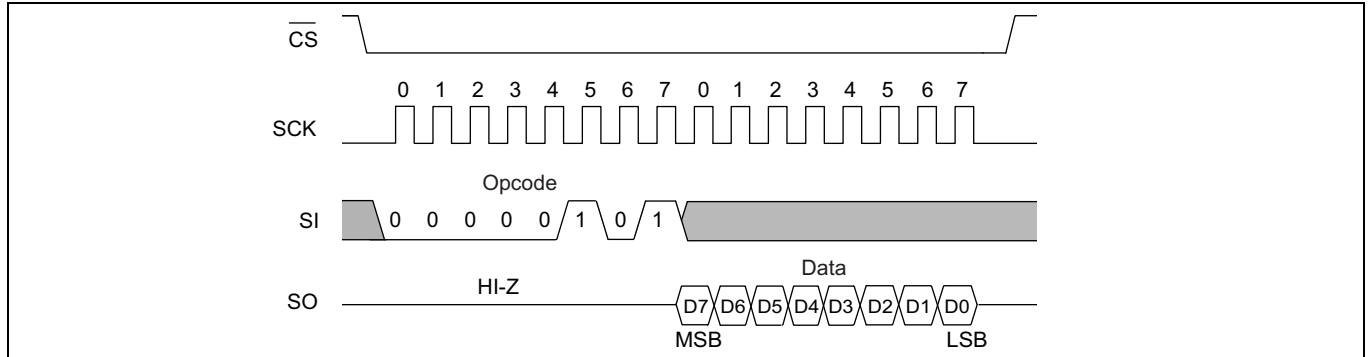


Figure 9 RDSR Bus Configuration

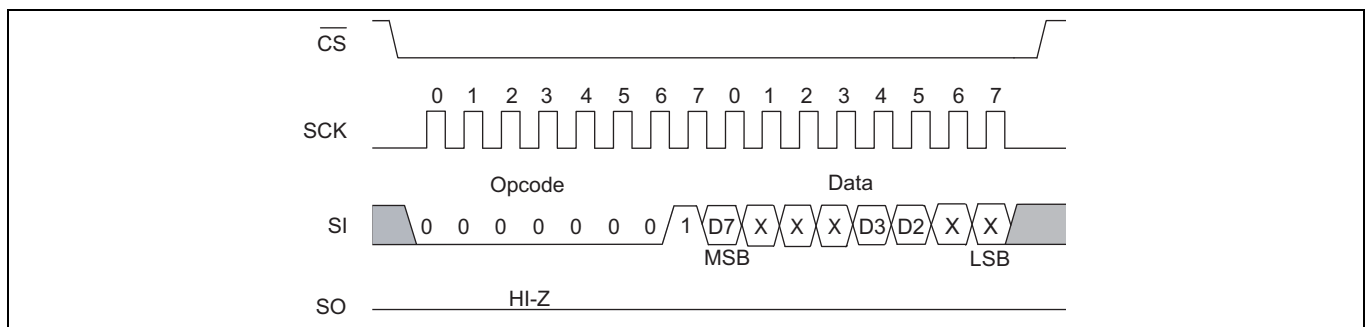


Figure 10 WRSR Bus Configuration (WREN not shown)

5 Memory operation

The SPI interface, which is capable of a high clock frequency, highlights the fast write capability of the F-RAM technology. Unlike serial flash and EEPROMs, the FM25V20A can perform sequential writes at bus speed. No page register is needed and any number of sequential writes may be performed.

5.1 Write operation

All writes to the memory begin with a WREN opcode with \overline{CS} being asserted and deasserted. The next opcode is WRITE. The WRITE opcode is followed by a three-byte address containing the 18-bit address (A17–A0) of the first data byte to be written into the memory. The upper six bits of the three-byte address are ignored. Subsequent bytes are data bytes, which are written sequentially. Addresses are incremented internally as long as the bus master continues to issue clocks and keeps \overline{CS} LOW. If the last address of 3FFFFh is reached, the counter will roll over to 00000h. Data is written MSB first. The rising edge of \overline{CS} terminates a write operation. A write operation is shown in [Figure 11](#).

Note: When a burst write reaches a protected block address, the automatic address increment stops and all the subsequent data bytes received for write will be ignored by the device.

EEPROMs use page buffers to increase their write throughput. This compensates for the technology’s inherently slow write operations. F-RAM memories do not have page buffers because each byte is written to the F-RAM array immediately after it is clocked in (after the eighth clock). This allows any number of bytes to be written without page buffer delays.

Note: If the power is lost in the middle of the write operation, only the last completed byte will be written.

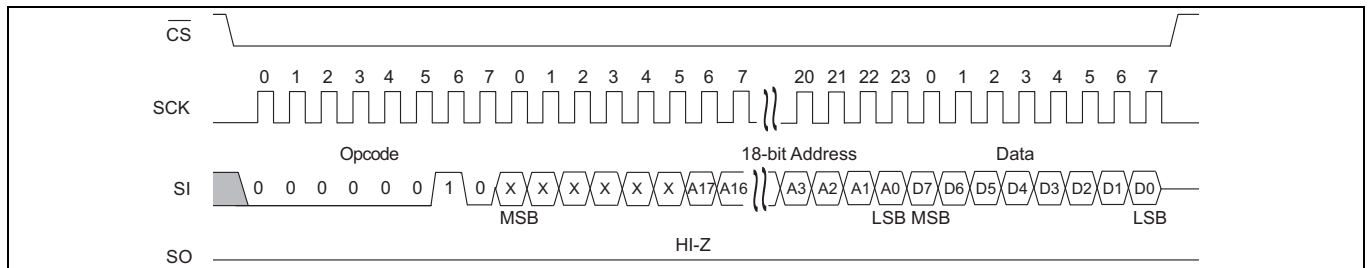


Figure 11 Memory Write (WREN not shown) operation

5.2 Read operation

After the falling edge of \overline{CS} , the bus master can issue a READ opcode. Following the READ command is a three-byte address containing the 18-bit address (A17–A0) of the first byte of the read operation. The upper six bits of the address are ignored. After the opcode and address are issued, the device drives out the read data on the next eight clocks. The SI input is ignored during read data bytes. Subsequent bytes are data bytes, which are read out sequentially. Addresses are incremented internally as long as the bus master continues to issue clocks and \overline{CS} is LOW. If the last address of 3FFFFh is reached, the counter will roll over to 00000h. Data is read MSB first. The rising edge of \overline{CS} terminates a read operation and tristates the SO pin. A read operation is shown in [Figure 12](#).

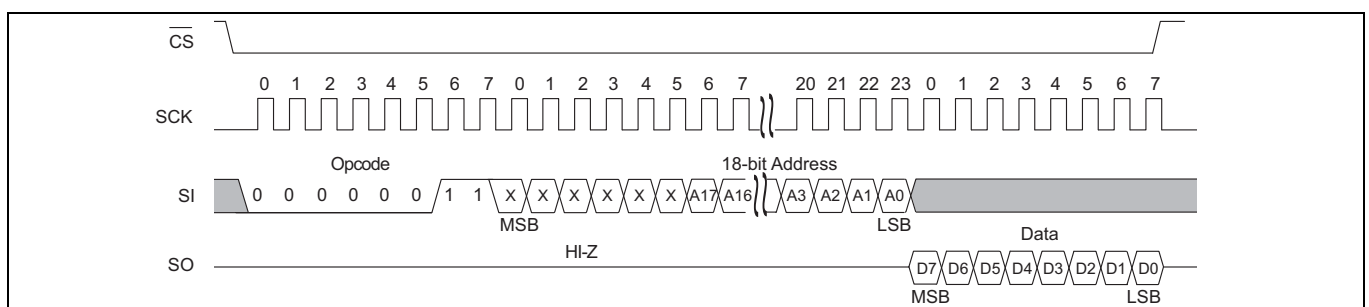


Figure 12 Memory Read operation

5.3 Fast Read operation

The FM25V20A supports a FAST READ opcode (0Bh) that is provided for code compatibility with serial flash devices. The FAST READ opcode is followed by a three-byte address containing the 18-bit address (A17–A0) of the first byte of the read operation and then a dummy byte. The dummy byte inserts a read latency of 8-clock cycle. The fast read operation is otherwise the same as an ordinary read operation except that it requires an additional dummy byte. After receiving opcode, address, and a dummy byte, the FM25V20A starts driving its SO line with data bytes, with MSB first, and continues transmitting as long as the device is selected and the clock is available. In case of bulk read, the internal address counter is incremented automatically, and after the last address 3FFFh is reached, the counter rolls over to 00000h. When the device is driving data on its SO line, any transition on its SI line is ignored. The rising edge of CS terminates a fast read operation and tristates the SO pin. A Fast Read operation is shown in **Figure 13**.

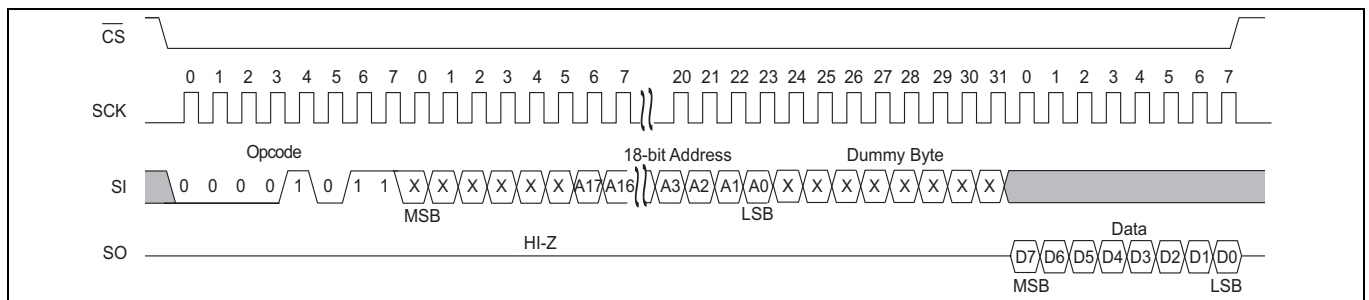


Figure 13 Fast Read operation

5.4 Sleep Mode

A low-power sleep mode is implemented on the FM25V20A device. The device will enter the low-power state when the SLEEP opcode B9h is clocked in and a rising edge of CS is applied. When in sleep mode, the SCK and SI pins are ignored and SO will be HI-Z, but the device continues to monitor the CS pin. On the next falling edge of CS, the device will return to normal operation within t_{REC} time. The SO pin remains in a HI-Z state during the wakeup period. The device does not necessarily respond to an opcode within the wakeup period. To start the wakeup procedure, the controller may send a “dummy” read, for example, and wait the remaining t_{REC} time.

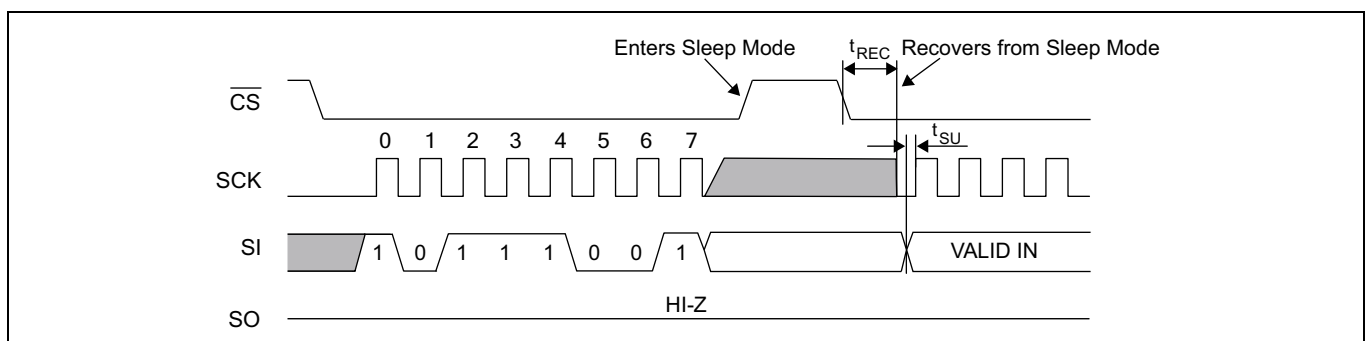


Figure 14 Sleep Mode operation

Memory operation

5.5 Device ID

The FM25V20A device can be interrogated for its manufacturer, product identification, and die revision. The RDID opcode 9Fh allows the user to read the manufacturer ID and product ID, both of which are read-only bytes. The JEDEC-assigned manufacturer ID places the Infineon (Ramtron) identifier in bank 7; therefore, there are six bytes of the continuation code 7Fh followed by the single byte C2h. There are two bytes of product ID, which includes a family code, a density code, a sub code, and the product revision code.

Table 7 Device ID

| Device ID (9 bytes) | Device ID description | | | | | |
|------------------------|---|-------------------|------------------|-----------------|-----------------|-----------------|
| | 71-16 (56 bits) | 15-13 (3 bits) | 12-8 (5 bits) | 7-6 (2 bits) | 5-3 (3 bits) | 2-0 (3 bits) |
| | Manufacturer ID | Product ID | | | | |
| Family | | Density | Sub | Rev | Rsvd | |
| 7F7F7F7F7F7FC22508h | 0111111101111111011111101111110111111101111111011111110111111111011111111000010 | 001 | 00101 | 00 | 001 | 000 |

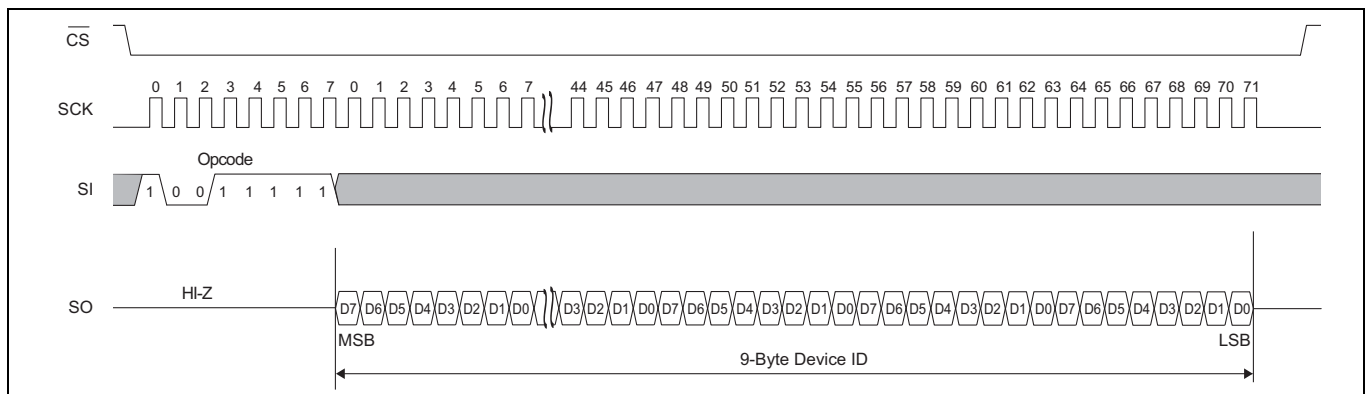


Figure 15 Read Device ID

5.6 Endurance

The FM25V20A devices are capable of being accessed at least 10^{14} times, reads or writes. An F-RAM memory operates with a read and restore mechanism. Therefore, an endurance cycle is applied on a row basis for each access (read or write) to the memory array. The F-RAM architecture is based on an array of rows and columns of 32K rows of 64-bits each. The entire row is internally accessed once, whether a single byte or all eight bytes are read or written. Each byte in the row is counted only once in an endurance calculation. **Table 8** shows endurance calculations for a 64-byte repeating loop, which includes an opcode, a starting address, and a sequential 64-byte data stream. This causes each byte to experience one endurance cycle through the loop. F-RAM read and write endurance is virtually unlimited even at a 40-MHz clock rate.

Table 8 Time to reach Endurance Limit for repeating 64-byte Loop

| SCK Freq (MHz) | Endurance Cycles/sec | Endurance Cycles/year | Years to reach Limit |
|----------------|----------------------|-----------------------|----------------------|
| 40 | 73,520 | 2.32×10^{12} | 43.1 |
| 10 | 18,380 | 5.79×10^{11} | 172.7 |
| 5 | 9,190 | 2.90×10^{11} | 345.4 |

6 Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. These user guidelines are not tested.

Table 9 Maximum ratings

| Parameter | Value |
|---|--|
| Storage temperature | -55°C to +125°C |
| Maximum accumulated storage time | |
| At 125°C ambient temperature | 1000 h |
| At 85°C ambient temperature | 10 Years |
| Ambient temperature with power applied | -55°C to +125°C |
| Supply voltage on V_{DD} relative to V_{SS} | -1.0 V to +4.5 V |
| Input voltage | -1.0 V to +4.5 V and $V_{IN} < V_{DD} + 1.0 V$ |
| DC voltage applied to outputs in High-Z state | -0.5 V to $V_{DD} + 0.5 V$ |
| Transient voltage (< 20 ns) on any pin to ground potential | -2.0 V to $V_{DD} + 2.0 V$ |
| Package power dissipation capability ($T_A = 25^\circ\text{C}$) | 1.0 W |
| Surface mount lead soldering temperature (3 seconds) | +260°C |
| DC output current (1 output at a time, 1 second duration) | 15 mA |
| Electrostatic Discharge Voltage | |
| Human Body Model (JEDEC Std JESD22-A114-B) | 2 kV |
| Charged Device Model (JEDEC Std JESD22-C101-A) | 500 V |
| Latch-up current | > 140 mA |

Operating range

7 Operating range

Table 10 **Operating range**

| Range | Ambient Temperature (T_A) | V_{DD} |
|--------------|--|-----------------------|
| Industrial | -40°C to +85°C | 2.0 V to 3.6 V |

8 DC electrical characteristics

Table 11 DC electrical characteristics

Over the **Operating range**

| Parameter | Description | Test conditions | Min | Typ ^[2] | Max | Unit | |
|------------------|---------------------------------|---|---------------------------|--------------------|-----------------------|------|----|
| V _{DD} | Power supply | | 2.0 | 3.3 | 3.6 | V | |
| I _{DD} | V _{DD} supply current | SCK toggling between V _{DD} - 0.2 V and V _{SS} , other inputs V _{SS} or V _{DD} - 0.2 V. SO = Open | f _{SCK} = 1 MHz | - | 0.5 | 0.80 | mA |
| | | | f _{SCK} = 40 MHz | - | 2.4 | 3 | mA |
| I _{SB} | V _{DD} standby current | CS = V _{DD} . All other inputs V _{SS} or V _{DD} . | T _A = 25°C | - | 100 | 150 | μA |
| | | | T _A = 85°C | - | - | 250 | μA |
| I _{ZZ} | Sleep mode current | CS = V _{DD} . All other inputs V _{SS} or V _{DD} . | T _A = 25°C | - | 3 | 5 | μA |
| | | | T _A = 85°C | - | - | 8 | μA |
| I _{LI} | Input leakage current | V _{SS} ≤ V _{IN} ≤ V _{DD} | - | - | ±1 | μA | |
| I _{LO} | Output leakage current | V _{SS} ≤ V _{OUT} ≤ V _{DD} | - | - | ±1 | μA | |
| V _{IH} | Input HIGH voltage | - | 0.7 × V _{DD} | - | V _{DD} + 0.3 | V | |
| V _{IL} | Input LOW voltage | - | -0.3 | - | 0.3 × V _{DD} | V | |
| V _{OH1} | Output HIGH voltage | I _{OH} = -1 mA, V _{DD} = 2.7 V. | 2.4 | - | - | V | |
| V _{OH2} | Output HIGH voltage | I _{OH} = -100 μA | V _{DD} - 0.2 | - | - | V | |
| V _{OL1} | Output LOW voltage | I _{OL} = 2 mA, V _{DD} = 2.7 V | - | - | 0.4 | V | |
| V _{OL2} | Output LOW voltage | I _{OL} = 150 μA | - | - | 0.2 | V | |

Note

2. Typical values are at 25°C, V_{DD} = V_{DD}(typ). Not 100% tested.

9 Data retention and endurance

Table 12 Data retention and endurance

| Parameter | Description | Test condition | Min | Max | Unit |
|-----------------|----------------|----------------------------|------------------|-----|--------|
| T _{DR} | Data retention | T _A = 85°C | 10 | – | Years |
| | | T _A = 75°C | 38 | – | Years |
| | | T _A = 65°C | 151 | – | Years |
| NV _C | Endurance | Over operating temperature | 10 ¹⁴ | – | Cycles |

Capacitance

10 Capacitance

Table 13 Capacitance

| Parameter ^[3] | Description | Test conditions | Max | Unit |
|--------------------------|-----------------------------|---|-----|------|
| C _O | Output pin capacitance (SO) | T _A = 25°C, f = 1 MHz, V _{DD} = V _{DD} (typ) | 8 | pF |
| C _I | Input pin capacitance | | 6 | pF |

Note

3. This parameter is periodically sampled and not 100% tested.

Thermal resistance

11 Thermal resistance

Table 14 Thermal resistance

| Parameter | Description | Test conditions | 8-pin SOIC | 8-pin DFN | Unit |
|---------------|--|--|------------|-----------|------|
| θ_{JA} | Thermal resistance (Junction to ambient) | Test conditions follow standard test methods and procedures for measuring thermal impedance, per EIA/JESD51. | 114 | 30 | °C/W |
| θ_{JC} | Thermal resistance (Junction to case) | | 40 | 11 | °C/W |

AC test conditions

12 AC test conditions

Table 15 AC test conditions

| Parameter | Value |
|--|-------------------------|
| Input pulse levels | 10% and 90% of V_{DD} |
| Input rise and fall times | 3 ns |
| Input and output timing reference levels | $0.5 \times V_{DD}$ |
| Output load capacitance | 30 pF |

13 AC switching characteristics

Table 16 AC switching characteristics

Over the **Operating range**

| Parameters ^[4] | | Description | V _{DD} = 2.0 V to 2.7 V | | V _{DD} = 2.7 V to 3.6 V | | Unit |
|-----------------------------------|-------------------|------------------------|----------------------------------|-----|----------------------------------|-----|------|
| Infineon Parameter | Alt. Parameter | | Min | Max | Min | Max | |
| f _{SCK} | – | SCK clock frequency | 0 | 25 | 0 | 40 | MHz |
| t _{CH} | – | Clock HIGH time | 18 | – | 11 | – | ns |
| t _{CL} | – | Clock LOW time | 18 | – | 11 | – | ns |
| t _{CSU} | t _{CSS} | Chip select setup | 12 | – | 10 | – | ns |
| t _{CSH} | t _{CSH} | Chip select hold | 12 | – | 10 | – | ns |
| t _{OD} ^[5, 6] | t _{HZCS} | Output disable time | – | 20 | – | 12 | ns |
| t _{ODV} | t _{CO} | Output data valid time | – | 16 | – | 9 | ns |
| t _{OH} | – | Output hold time | 0 | – | 0 | – | ns |
| t _D | – | Deselect time | 60 | – | 40 | – | ns |
| t _{SU} | t _{SD} | Data setup time | 8 | – | 5 | – | ns |
| t _H | t _{HD} | Data hold time | 8 | – | 5 | – | ns |

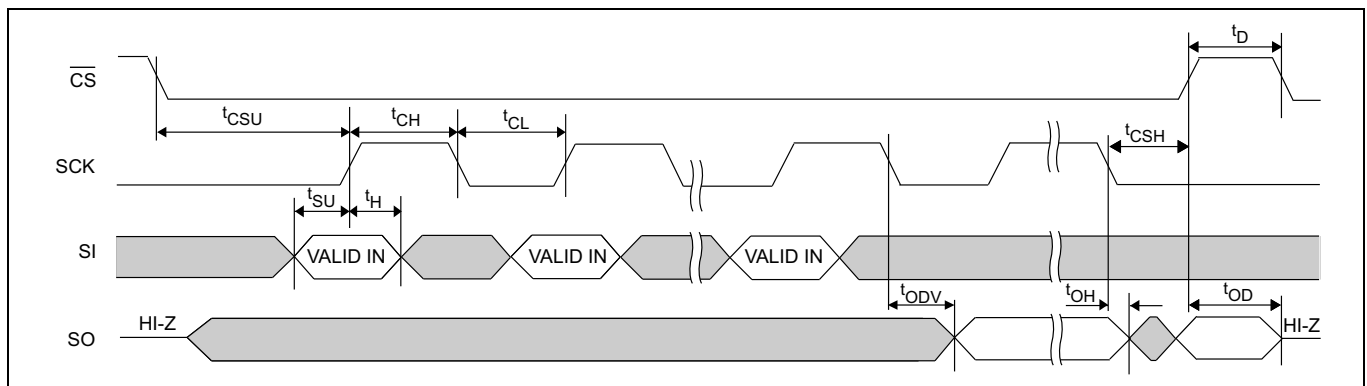


Figure 16 Synchronous Data Timing (Mode 0)

Notes

- Test conditions assume a signal transition time of 3 ns or less, timing reference levels of $0.5 \times V_{DD}$, input pulse levels of 10% to 90% of V_{DD} , and output loading of the specified I_{OL}/I_{OH} and 30 pF load capacitance shown in **“AC test conditions”** on page 23.
- t_{OD} and t_{HZ} are specified with a load capacitance of 5 pF. Transition is measured when the outputs enter a high impedance state
- Characterized but not 100% tested in production.

14 Power Cycle Timing

Table 17 Power Cycle Timing

Over the **Operating range**

| Parameter | Description | Min | Max | Unit |
|-----------------|--|-----|-----|------------------------|
| t_{PU} | Power-up $V_{DD}(\text{min})$ to first access (\overline{CS} LOW) | 1 | – | ms |
| t_{PD} | Last access (\overline{CS} HIGH) to power-down ($V_{DD}(\text{min})$) | 0 | – | μs |
| $t_{VR}^{[7]}$ | V_{DD} power-up ramp rate | 50 | – | $\mu\text{s}/\text{V}$ |
| $t_{VF}^{[7]}$ | V_{DD} power-down ramp rate | 100 | – | $\mu\text{s}/\text{V}$ |
| $t_{REC}^{[8]}$ | Recovery time from sleep mode | – | 450 | μs |

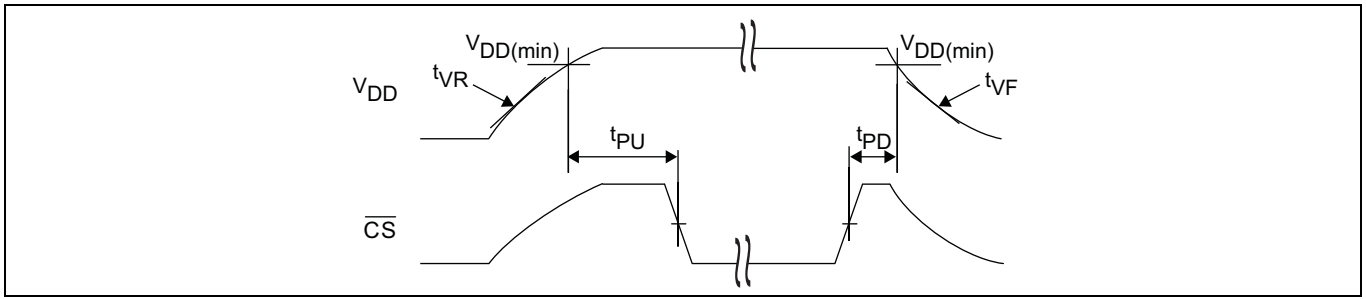


Figure 17 Power Cycle Timing

Notes

- Slope measured at any point on the V_{DD} waveform.
- Guaranteed by design. Refer to **Figure 14** for sleep mode recovery timing.

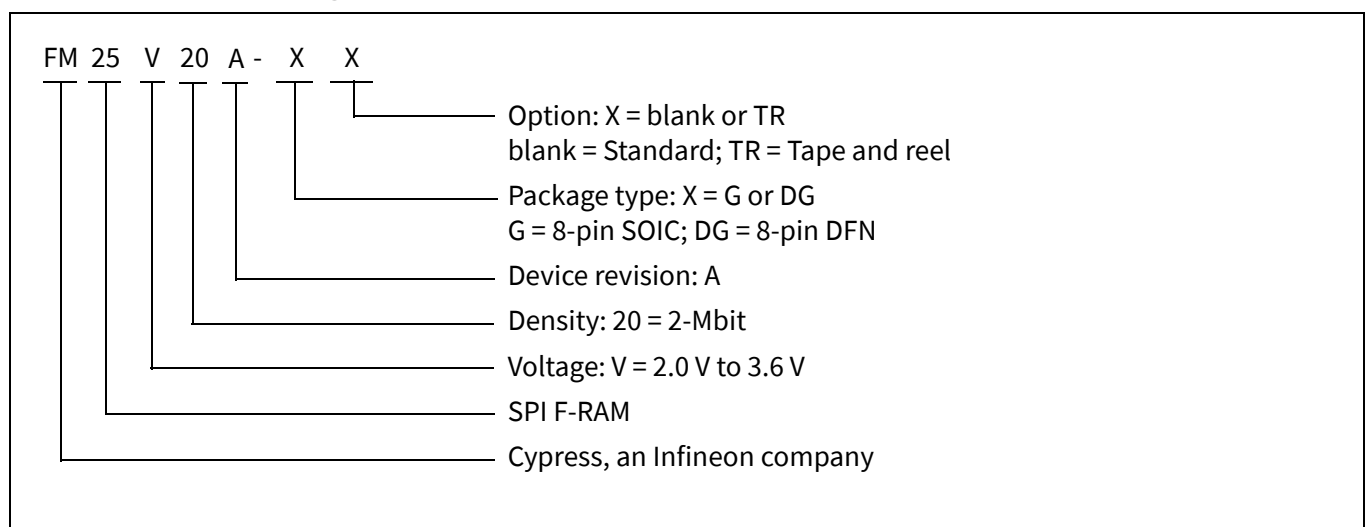
15 Ordering information

Table 18 Ordering information

| Product | Package diagram | Package type | Operating range |
|---------------|-----------------|--------------|-----------------|
| FM25V20A-G | 001-85261 | 8-pin SOIC | Industrial |
| FM25V20A-GTR | | | Industrial |
| FM25V20A-DG | 001-85579 | 8-pin DFN | Industrial |
| FM25V20A-DGTR | | | Industrial |

All these parts are Pb-free. Contact your local Cypress sales representative for availability of these parts.

15.1 Ordering code definitions



16 Package diagrams

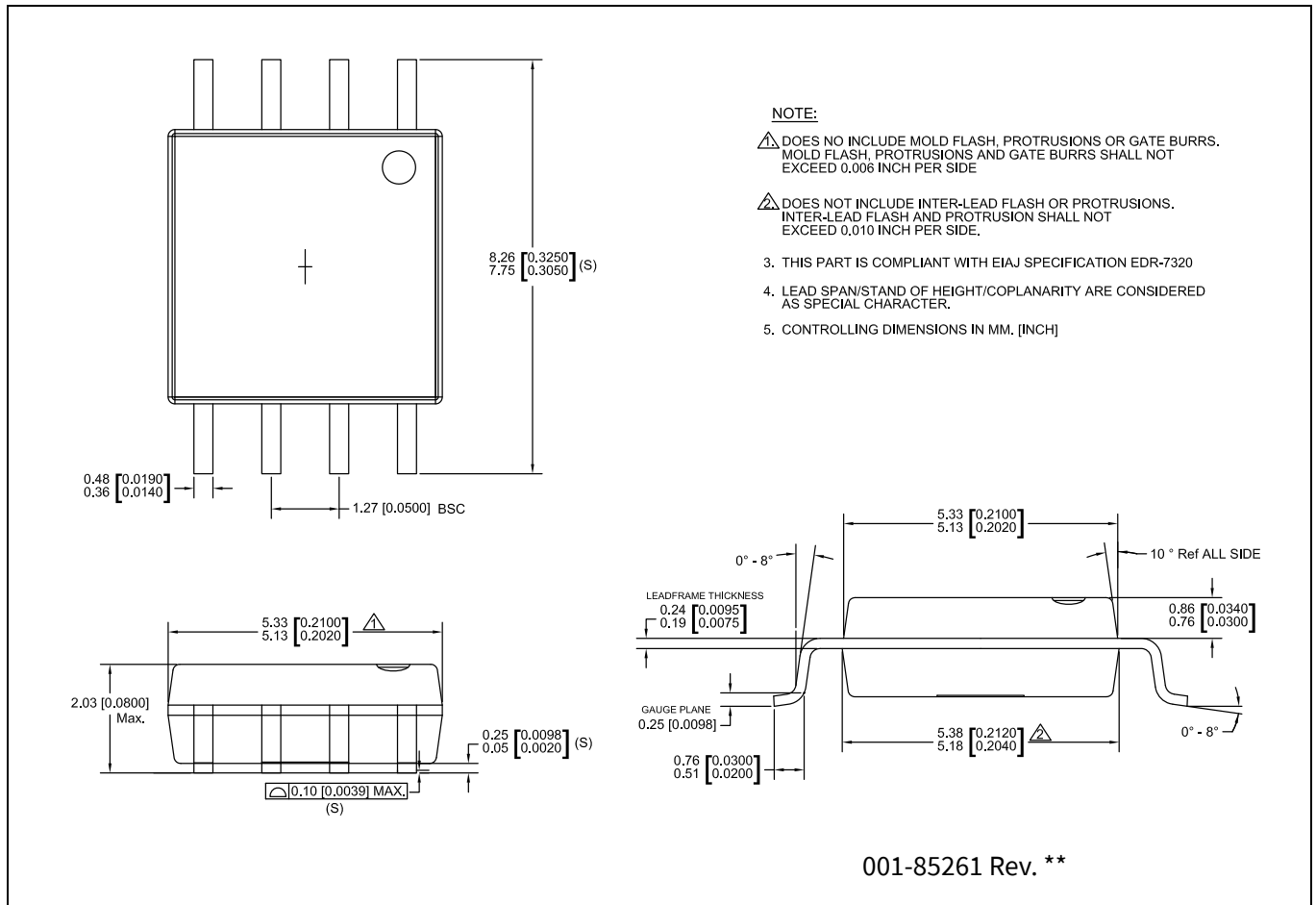


Figure 18 8-pin SOIC (208 Mils) SZ820 package outline (PG-DSO-8), 001-85261

2-Mbit (256K × 8) Serial (SPI) F-RAM
serial (SPI), 256K × 8, 40 MHz, industrial



Package diagrams

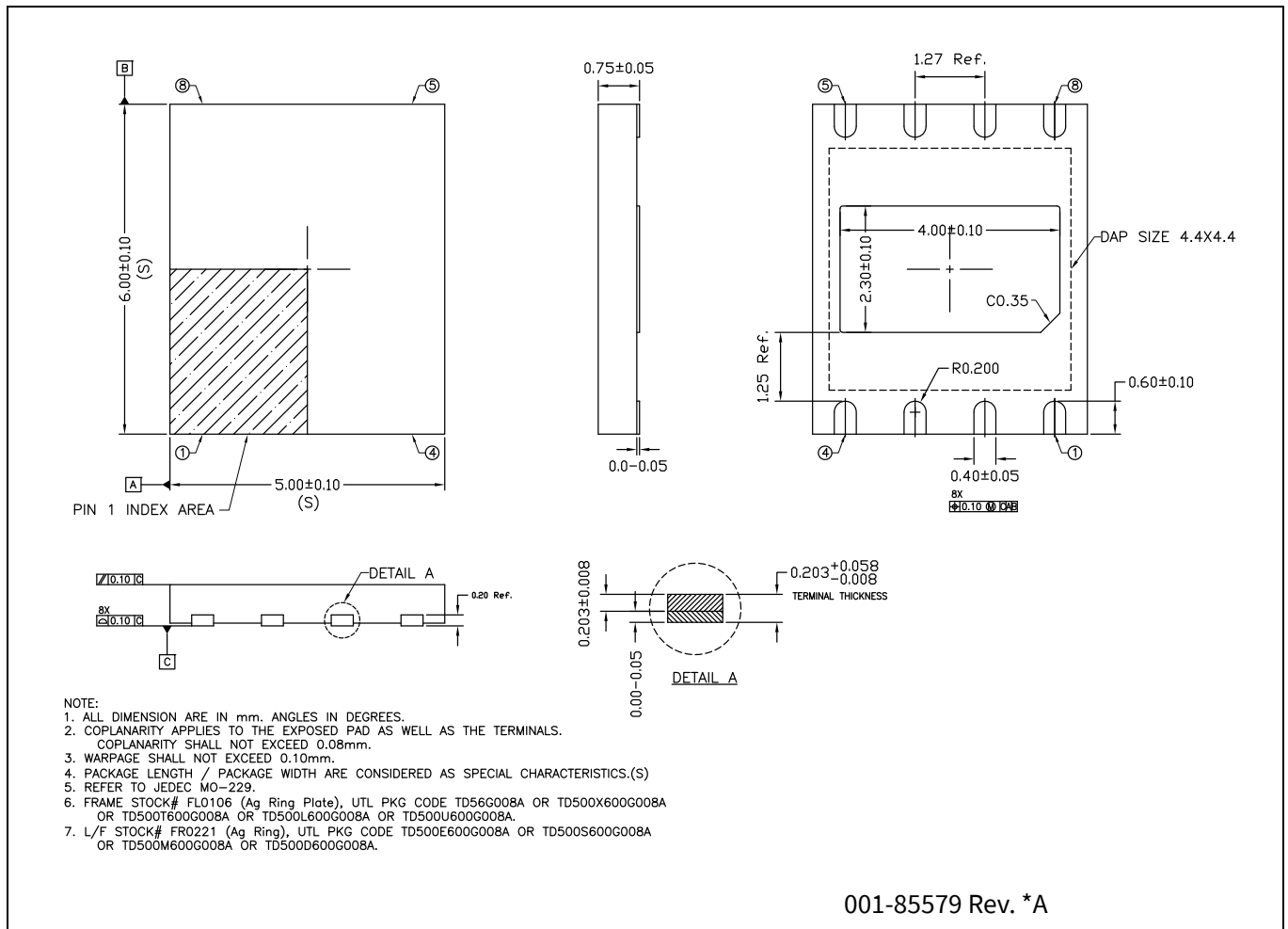


Figure 19 8-pin DFN (5 mm × 6 mm × 0.75 mm) LH08D package outline (PG-USON-8), 001-85579

17 Acronyms

Table 19 Acronyms used in this document

| Acronym | Description |
|----------------|---|
| CPHA | Clock Phase |
| CPOL | Clock Polarity |
| EEPROM | Electrically Erasable Programmable Read-Only Memory |
| EIA | Electronic Industries Alliance |
| F-RAM | Ferroelectric Random Access Memory |
| I/O | Input/Output |
| JEDEC | Joint Electron Devices Engineering Council |
| JESD | JEDEC standards |
| LSB | Least Significant Bit |
| MSB | Most Significant Bit |
| RoHS | Restriction of Hazardous Substances |
| SPI | Serial Peripheral Interface |
| SOIC | Small Outline Integrated Circuit |
| DFN | Dual Flat No-lead |

18 Document conventions

18.1 Units of measure

Table 20 Units of measure

| Symbol | Unit of measure |
|---------------|------------------------|
| °C | degree Celsius |
| Hz | hertz |
| kHz | kilohertz |
| kΩ | kilohm |
| Mbit | megabit |
| MHz | megahertz |
| μA | microampere |
| μF | microfarad |
| μs | microsecond |
| mA | milliampere |
| ms | millisecond |
| ns | nanosecond |
| Ω | ohm |
| % | percent |
| pF | picofarad |
| V | volt |
| W | watt |

Revision history

| Document revision | Date | Description of changes |
|-------------------|------------|---|
| ** | 2014-01-23 | New data sheet. |
| *A | 2014-05-07 | <p>Changed status from Preliminary to Final.</p> <p>Updated Maximum Ratings:</p> <p>Updated Table 9:</p> <p>Removed “Machine Model” under “Electrostatic Discharge Voltage”.</p> <p>Updated Thermal resistance:</p> <p>Updated Table 14:</p> <p>Changed value of Θ_{JA} corresponding to 8-pin TDFN package from 17°C/W to 30°C/W.</p> <p>Updated Ordering information:</p> <p>Updated Table 18:</p> <p>Removed FM25V20A-GES and FM25V20A-DGES part numbers.</p> |
| *B | 2014-05-14 | No technical updates. |
| *C | 2014-07-31 | <p>Updated Package diagrams:</p> <p>Updated 8-pin DFN package spec to the current revision.</p> |
| *D | 2014-11-12 | <p>Updated Functional description:</p> <p>Added related documentation hyperlink at the end.</p> <p>Completing Sunset Review.</p> |
| *E | 2015-03-25 | <p>Replaced “TDFN” with “DFN” in all instances across the document.</p> <p>Updated Pin definitions:</p> <p>Updated Table 1:</p> <p>Updated details in “Description” column of “EXPOSED PAD” pin.</p> |
| *F | 2015-08-10 | <p>Updated Maximum Ratings:</p> <p>Updated Table 9:</p> <p>Removed “Maximum junction temperature”.</p> <p>Added “Maximum accumulated storage time”.</p> <p>Added “Ambient temperature with power applied”.</p> <p>Updated to new template.</p> |
| *G | 2017-06-19 | Updated Cypress Logo and copyright. |
| *H | 2019-05-15 | <p>Updated Logic block diagram:</p> <p>Removed HOLD pin.</p> <p>Updated Pinouts:</p> <p>Updated Figure 1 (Changed Pin 7 from $\overline{\text{HOLD}}$ to DNU).</p> <p>Updated Figure 2 (Changed Pin 7 from $\overline{\text{HOLD}}$ to DNU).</p> <p>Updated Pin definitions:</p> <p>Updated Table 1:</p> <p>Removed HOLD related information from “Description” column corresponding to SO pin.</p> <p>Removed HOLD pin and its description.</p> <p>Added DNU pin and its description.</p> <p>Updated Functional overview:</p> <p>Updated SPI overview:</p> <p>Updated Data Transmission (SI/SO):</p> <p>Removed HOLD pin related information.</p> <p>Updated Figure 3 (Removed HOLD pin connection).</p> <p>Updated Figure 4 (Removed HOLD pin connection).</p> |

2-Mbit (256K × 8) Serial (SPI) F-RAM
serial (SPI), 256K × 8, 40 MHz, industrial



Revision history

| Document revision | Date | Description of changes |
|-------------------|------------|---|
| *H (cont.) | 2019-05-15 | Updated Memory operation : Removed "HOLD Pin Operation". Updated AC switching characteristics : Updated Table 16 : Removed HOLD pin timings related information. Removed figure "HOLD Timing". Updated to new template. |
| *I | 2019-08-28 | Updated Features : Updated description. Updated DC electrical characteristics : Updated Table 11 : Changed typical value of I_{DD} parameter from 0.13 mA to 0.5 mA corresponding to Test condition " $f_{SCK} = 1$ MHz". Changed maximum value of I_{DD} parameter from 0.30 mA to 0.80 mA corresponding to Test condition " $f_{SCK} = 1$ MHz". Changed typical value of I_{DD} parameter from 1.4 mA to 2.4 mA corresponding to Test condition " $f_{SCK} = 40$ MHz". Updated AC switching characteristics : Updated Table 16 : Removed t_R , t_F parameters and its corresponding details. Removed Note "Rise and fall times measured between 10% and 90% of waveform." and its reference. |
| *J | 2023-12-22 | Updated Pin definitions : Updated Table 1 . Migrated to Infineon template. |

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